

BTA208X-1000C0

High commutation three-quadrant triacs

Rev. 01 — 3 September 2009

Product data sheet

1. Product profile

1.1 General description

Passivated high voltage, high commutation triac in a full pack, plastic package. This triac is intended for use in motor control circuits where high blocking voltage, high static and dynamic dV/dt as well as high dI_{com}/dt can occur. This device will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

1.2 Features and benefits

- 3Q technology with superior commutation performance for improved noise immunity
- Enhanced immunity to voltage transients and noise
- High false trigger immunity
- Isolated package
- Very high blocking voltage capability of 1000 V

1.3 Applications

- General purpose motor control
- Reversible induction motor control

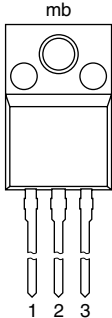

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	1000	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(initial)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; see Figure 4 and 5	-	-	65	A
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 73\text{ °C}$; see Figure 3 , 1 and 2	-	-	8	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 7	5	11	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 7	5	14	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 7	5	25	35	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p style="text-align: center;">SOT186A (TO-220F)</p>	
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

3. Ordering information

Table 3. Ordering information

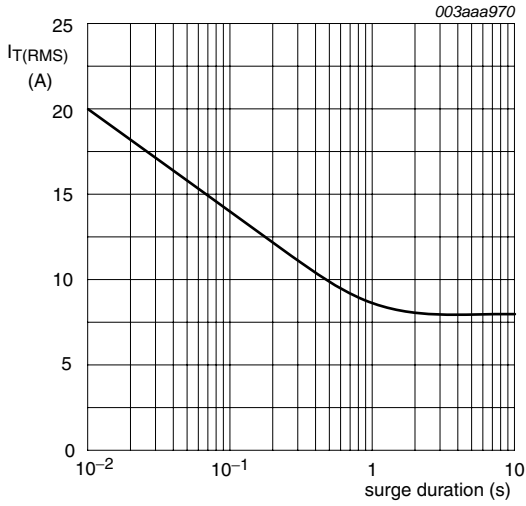
Type number	Package		Version
	Name	Description	
BTA208X-1000C0	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	1000	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 73\text{ °C}$; see Figure 3, 1 and 2	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; see Figure 4 and 5	-	65	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	71	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	21	A ² s
di_T/dt	rate of rise of on-state current	$I_T = 12\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	A/ μs
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power		-	0.5	W
T_{stg}	storage temperature		-40	150	°C
T_j	junction temperature		-	125	°C



$f = 50 \text{ Hz}$, $T_h = 73 \text{ }^\circ\text{C}$

Fig 1. RMS on-state current as a function of surge duration; maximum values

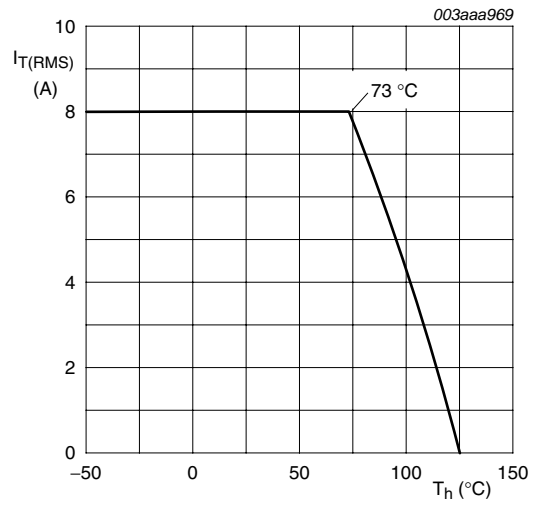


Fig 2. RMS on-state current as a function of heatsink temperature; maximum values

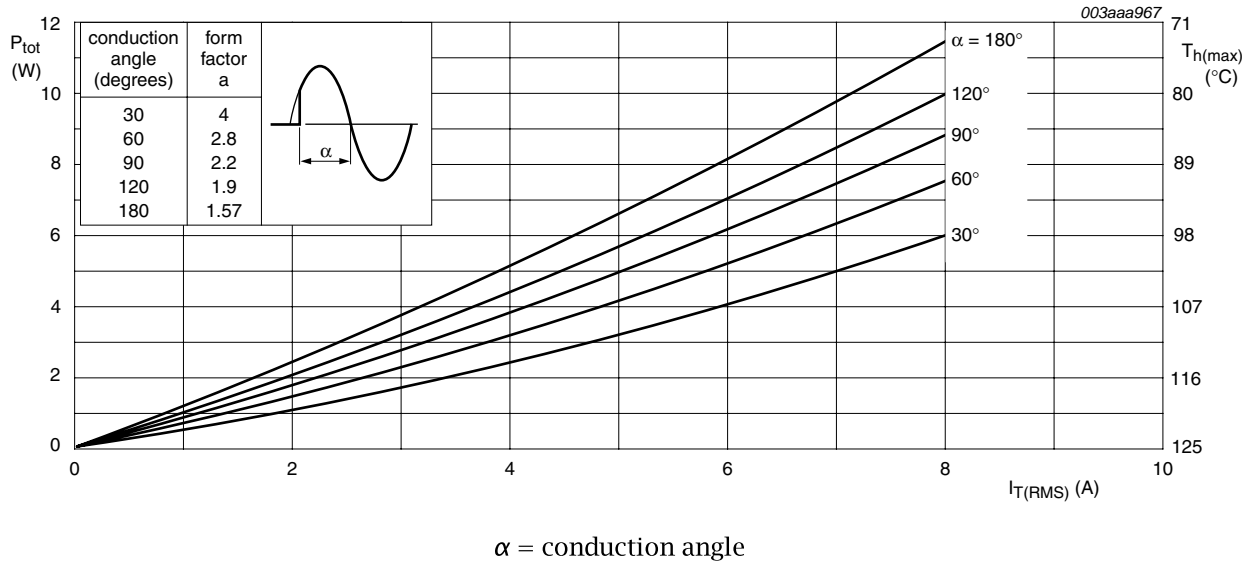
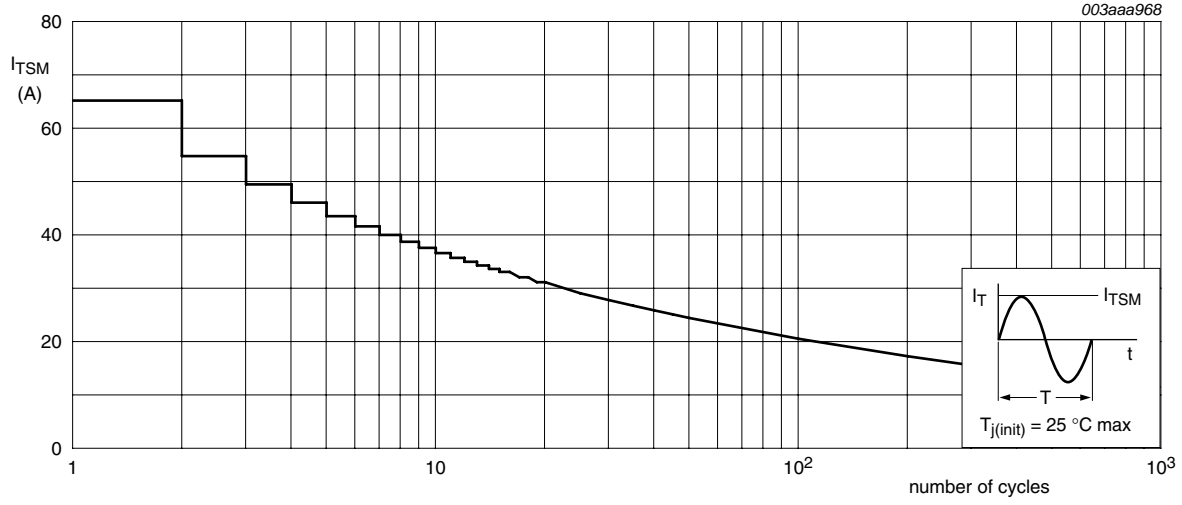
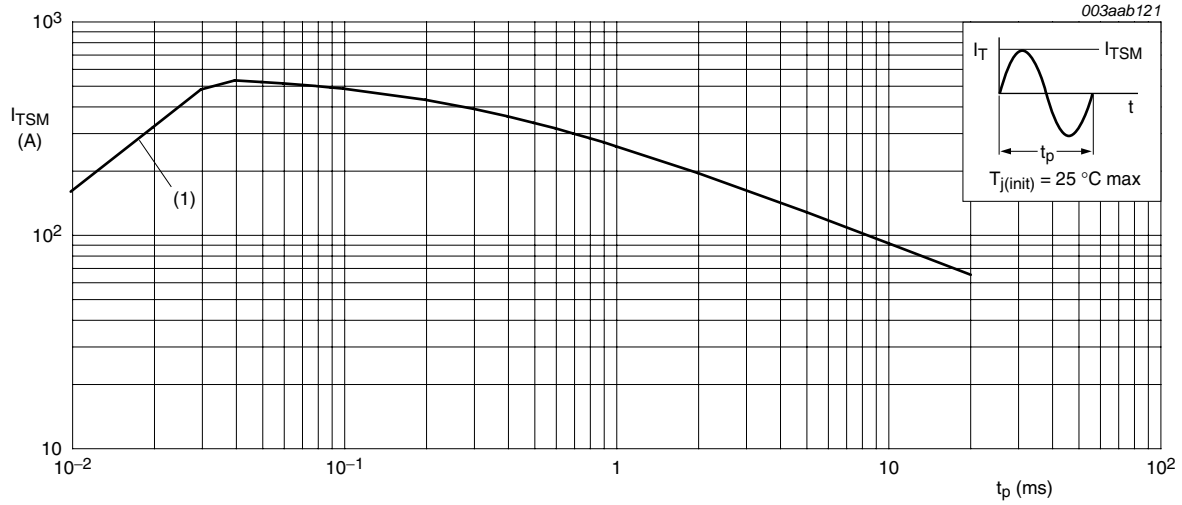


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values



$f = 50\text{ Hz}$

Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20\text{ ms(1) } dI_T/dt\text{ limit}$

Fig 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle with heatsink compound; see Figure 6	-	-	4.5	K/W
			-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	55	-	K/W

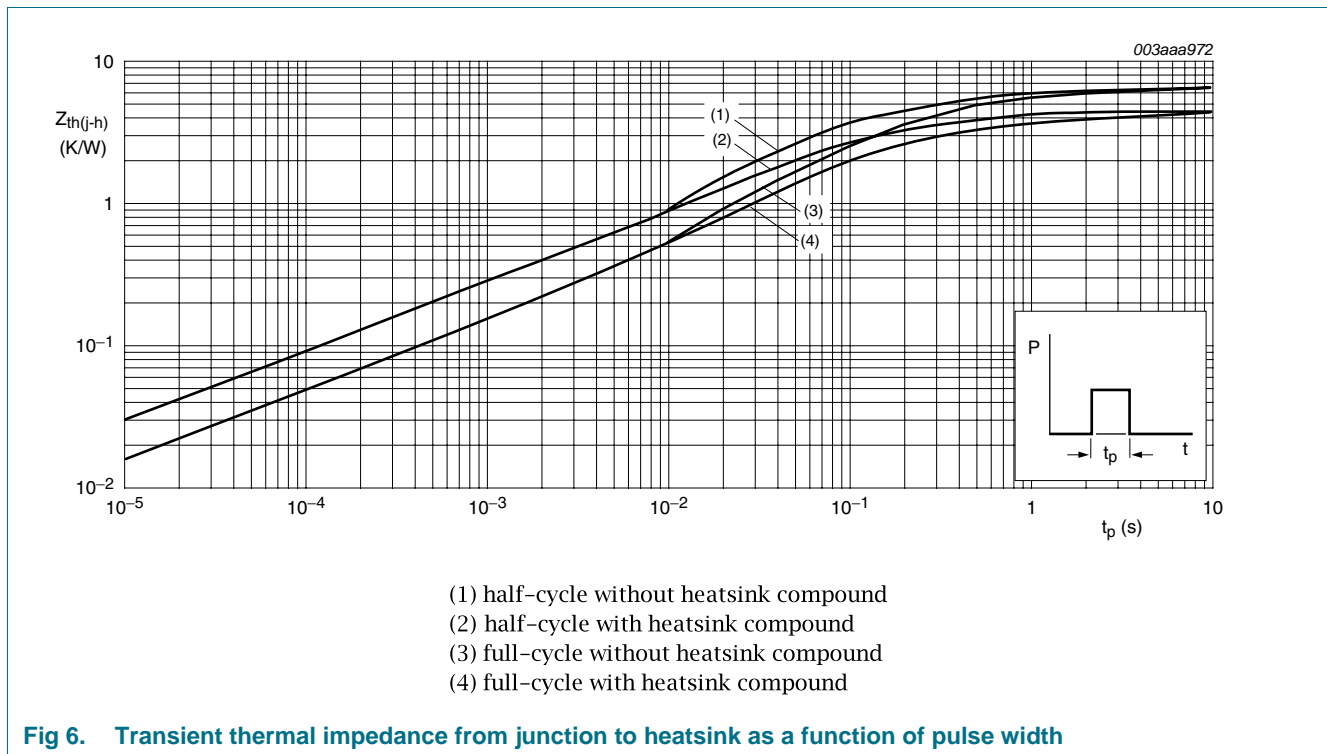


Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

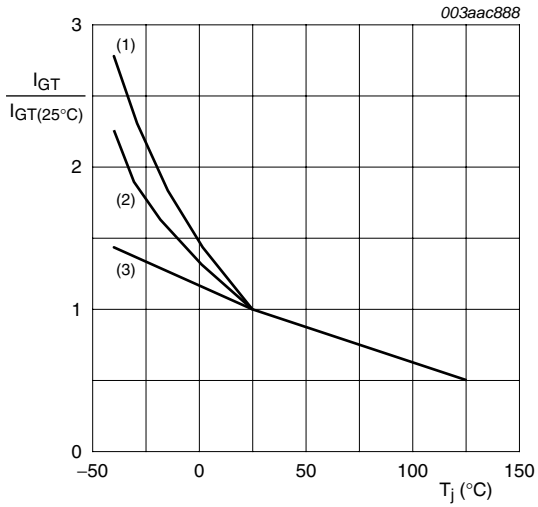
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; T _h = 25 °C	-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 7	5	11	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 7	5	14	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 7	5	25	35	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 8	-	25	50	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 8	-	48	75	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 8	-	30	50	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; see Figure 9	-	20	50	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_j = 25\text{ °C}$; see Figure 10	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; see Figure 11	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$	0.25	0.4	-	V
I_D	off-state current	$V_D = 1000\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 670\text{ V}$; $T_j = 125\text{ °C}$; exponential waveform; gate open circuit	1500	4000	-	V/ μ s
dl_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; gate open circuit; see Figure 12	12	32	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 12\text{ A}$; $V_D = 1000\text{ V}$; $I_G = 0.1\text{ A}$; $dl_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μ s



(1) T2- G-(2) T2+ G-(3) T2+ G+

Fig 7. Normalized gate trigger current as a function of junction temperature

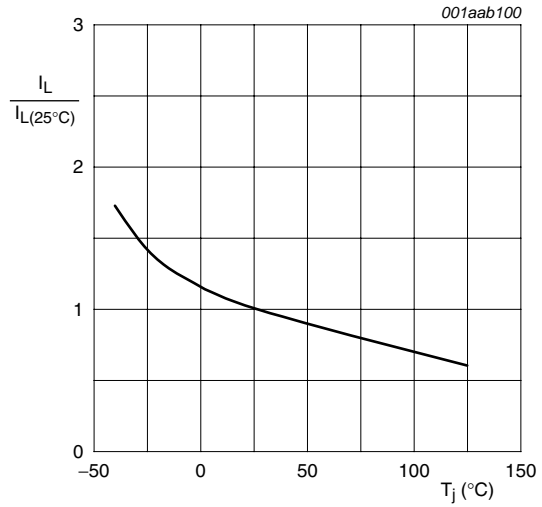


Fig 8. Normalized latching current as a function of junction temperature

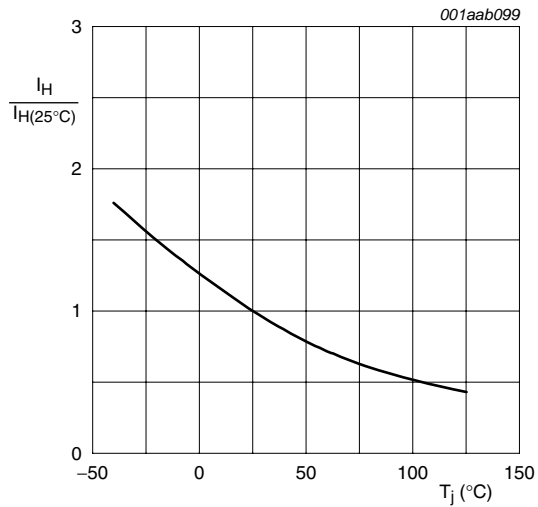
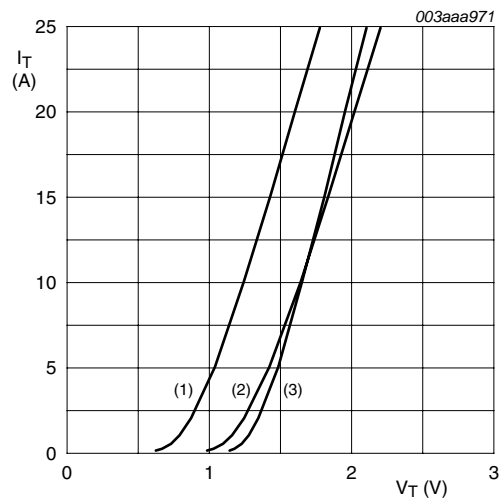


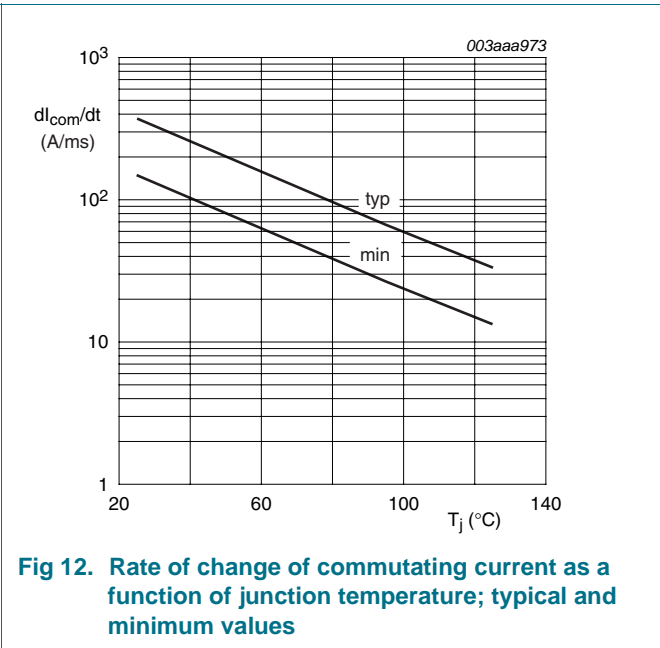
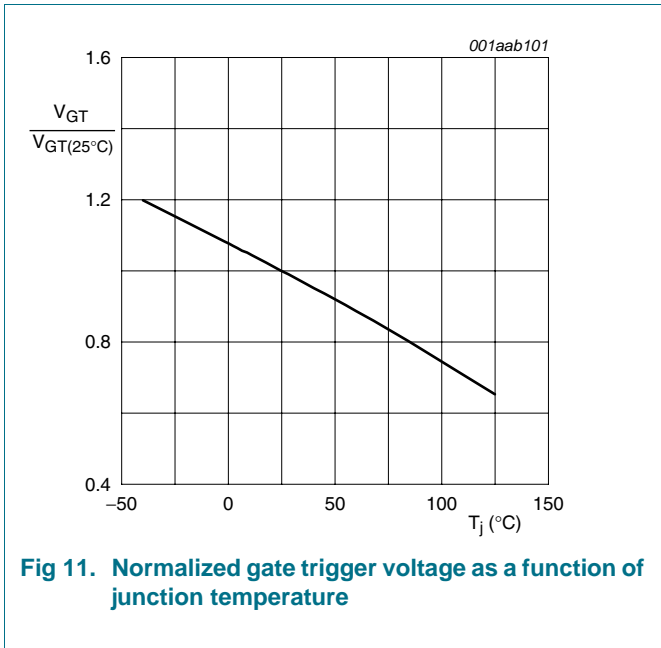
Fig 9. Normalized holding current as a function of junction temperature



$V_0 = 1.22 \text{ V}; R_s = 0.04 \Omega$

- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig 10. On-state current as a function of on-state voltage



8. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A

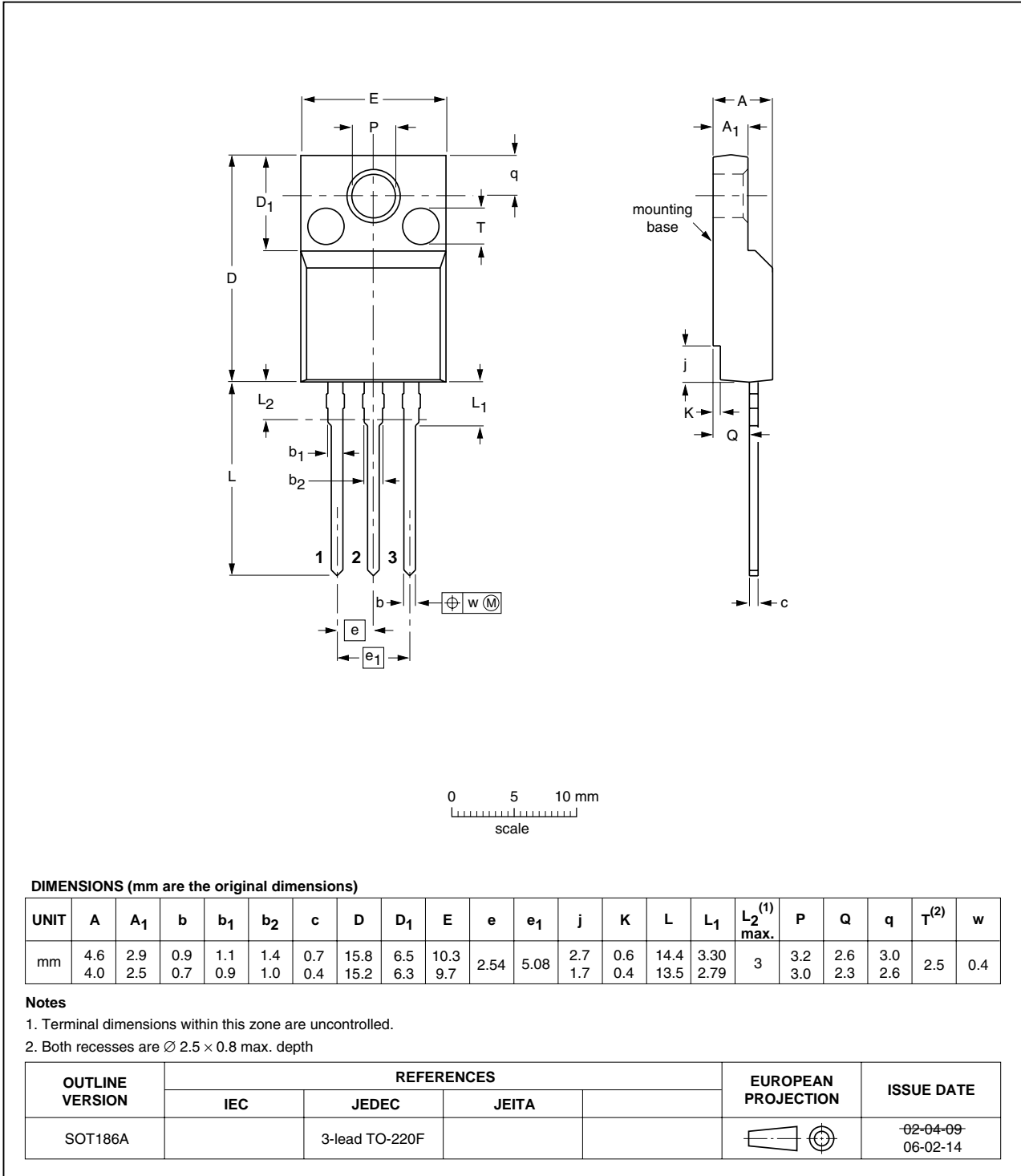


Fig 13. Package outline SOT186A (TO-220F)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA208X-1000C0_1	20090903	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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